

IN THE CLAIMS

Please amend the claims as follows:

Claims 1 – 11 (Cancelled)

12. (Currently Amended) A member for a semiconductor device, comprising:
a base member made of an alloy or composite mainly composed of Cu and W and/or Mo,
wherein a coating layer made of a hard carbon film is provided on at least a surface of the
base member on which another member for the semiconductor device is bonded with a resin, and
the coating layer has a thickness of about 0.5 to 1.5 μm .

13. (Previously Presented) The member for a semiconductor device according to
claim 12, wherein the alloy or composite mainly composed of Cu and W and/or Mo contains Cu
of 5 to 40% by weight.

14. (Currently Amended) A member for a semiconductor device, comprising:
a base member made of an alloy or composite mainly composed of Al-SiC,
wherein a coating layer made of a hard carbon film is provided on at least a surface of the
base member on which another member for the semiconductor device is bonded with a resin, and
the coating layer has a thickness of about 0.5 to 1.5 μm .

15. (Previously Presented) The member for a semiconductor device according to
claim 14, wherein the alloy or composite mainly composed of Al-SiC contains SiC of 10 to 70%
by weight.

16. (Currently Amended) A member for a semiconductor device, comprising:
a base member made of an alloy or composite mainly composed of Si-SiC,
wherein a coating layer made of a hard carbon film is provided on at least a surface of the
base member on which another member for the semiconductor device is bonded with a resin, and
the coating layer has a thickness of about 0.5 to 1.5 μm .

17. (Previously Presented) The member for a semiconductor device according to claim 16, wherein the alloy or composite mainly composed of Si-SiC contains Si of 10 to 35% by weight.

Claims 18-20. (Cancelled)

21. (Previously Presented) The member for a semiconductor device according to claim 12, wherein the surface of the base member on which the coating layer is formed has a surface roughness of 0.1 to 20 μm in R_{max} .

22. (Previously Presented) The member for a semiconductor device according to claim 14, wherein the surface of the base member on which the coating layer is formed has a surface roughness of 0.1 to 20 μm in R_{max} .

23. (Previously Presented) The member for a semiconductor device according to claim 16, wherein the surface of the base member on which the coating layer is formed has a surface roughness of 0.1 to 20 μm in R_{max} .

24. (Previously Presented) The member for a semiconductor device according to claim 12, wherein pores in the surface of the base member on which the coating layer is formed have a depth of 100 μm or less.

25. (Previously Presented) The member for a semiconductor device according to claim 14, wherein pores in the surface of the base member on which the coating layer is formed have a depth of 100 μm or less.

26. (Previously Presented) The member for a semiconductor device according to claim 16, wherein pores in the surface of the base member on which the coating layer is formed have a depth of 100 μm or less.

27. (Previously Presented) The member for a semiconductor device according to claim 12, wherein a plating layer of Ni is provided between the coating layer and the surface of the base member on which the coating layer is formed.

28. (Previously Presented) The member for a semiconductor device according to claim 14, wherein a plating layer of Ni is provided between the coating layer and the surface of the base member on which the coating layer is formed.

29. (Previously Presented) The member for a semiconductor device according to claim 16, wherein a plating layer of Ni is provided between the coating layer and the surface of the base member on which the coating layer is formed.

30. (Previously Presented) A semiconductor device employing the member for a semiconductor device according to claim 12.

31. (Previously Presented) A semiconductor device employing the member for a semiconductor device according to claim 14.

32. (Previously Presented) A semiconductor device employing the member for a semiconductor device according to claim 16.